

## Product Summary

$V_{(BR)DSS}$	$R_{DS(ON) \text{ max}}$	$I_D \text{ max}$ $T_A = 25^\circ\text{C}$
60V	7.5Ω @ $V_{GS} = 5V$	210mA

## Description and Applications

This MOSFET has been designed to minimize the on-state resistance ( $R_{DS(on)}$ ) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Motor control
- Power Management Functions

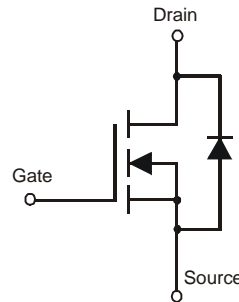
## Features and Benefits

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Small Surface Mount Package
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Notes 3 & 4)**
- **Qualified to AEC-Q101 standards for High Reliability**

## Mechanical Data

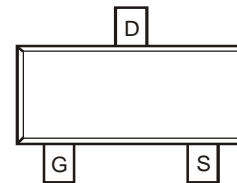
- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish annealed over Alloy 42 leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Weight: 0.008 grams (approximate)

SOT23



Top View

Equivalent Circuit



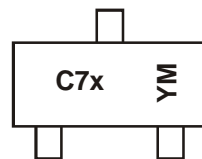
Top View

## Ordering Information (Note 5)

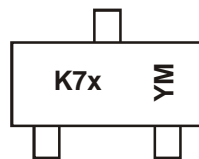
Part Number	Qualification	Case	Packaging
2N7002-7-F	Commercial	SOT23	3,000/Tape & Reel
2N7002-13-F	Commercial	SOT23	10,000/Tape & Reel
2N7002Q-7-F	Automotive	SOT23	3,000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
  2. See <http://www.diodes.com> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. Product manufactured with Date Code V12 (week 50, 2008) and newer are built with Green Molding Compound. Product manufactured prior to Date Code V12 are built with Non-Green Molding Compound and may contain Halogens or  $Sb_2O_3$  Fire Retardants.
  5. For packaging details, go to our website at <http://www.diodes.com>.

## Marking Information



Chengdu A/T Site



Shanghai A/T Site

K = SAT (Shanghai Assembly/ Test site)  
 C = CAT (Chengdu Assembly/ Test site)  
 7x= Product Type Marking Code  
 YM = Date Code Marking  
 Y = Year (ex: N = 2002)  
 M = Month (ex: 9 = September)

### Date Code Key

Year	2002	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012	2013	2014	2015	2016	2017
Code	N	P	R	S	T	U	V	W	X	Y	Z	A	B	C	D	E
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec				
Code	1	2	3	4	5	6	7	8	9	O	N	D				

**Maximum Ratings** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic		Symbol	Value	Units
Drain-Source Voltage		V <sub>DSS</sub>	60	V
Drain-Gate Voltage R <sub>GS</sub> ≤ 1.0MΩ		V <sub>DGR</sub>	60	V
Gate-Source Voltage		V <sub>GSS</sub>	±20	V
			±40	
Continuous Drain Current (Note 6) V <sub>GS</sub> = 10V	Steady State	T <sub>A</sub> = 25°C	170	mA
		T <sub>A</sub> = 85°C	120	
		T <sub>A</sub> = 100°C	105	
Continuous Drain Current (Note 7) V <sub>GS</sub> = 10V	Steady State	T <sub>A</sub> = 25°C	210	mA
		T <sub>A</sub> = 85°C	150	
		T <sub>A</sub> = 100°C	135	
Maximum Body Diode Forward Current (Note 7)	Pulsed	I <sub>S</sub>	0.5	A
			Continuous	
Pulsed Drain Current (10μs pulse, duty cycle = 1%)		I <sub>DM</sub>	800	mA

**Thermal Characteristics** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic		Symbol	Value	Units
Total Power Dissipation	(Note 6)	P <sub>D</sub>	370	mW
	(Note 7)		540	
Thermal Resistance, Junction to Ambient	(Note 6)	R <sub>θJA</sub>	348	°C/W
	(Note 7)		241	
Thermal Resistance, Junction to Case	(Note 7)	R <sub>θJC</sub>	91	°C
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to 150	°C

**Electrical Characteristics** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 8)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	60	70	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 10μA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	1.0	μA	V <sub>DS</sub> = 60V, V <sub>GS</sub> = 0V
				500		
Gate-Body Leakage	I <sub>GSS</sub>	—	—	±10	nA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 8)</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	1.0	—	2.5	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	3.2	7.5	Ω	V <sub>GS</sub> = 5.0V, I <sub>D</sub> = 0.05A
			4.4	13.5		
On-State Drain Current	I <sub>D(ON)</sub>	0.5	1.0	—	A	V <sub>GS</sub> = 10V, V <sub>DS</sub> = 7.5V
Forward Transconductance	g <sub>FS</sub>	80	—	—	mS	V <sub>DS</sub> = 10V, I <sub>D</sub> = 0.2A
Diode Forward Voltage	V <sub>SD</sub>	—	0.78	1.5	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 115mA
<b>DYNAMIC CHARACTERISTICS (Note 9)</b>						
Input Capacitance	C <sub>ISS</sub>	—	22	50	pF	V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V f = 1.0MHz
Output Capacitance	C <sub>OSS</sub>	—	11	25	pF	
Reverse Transfer Capacitance	C <sub>RSS</sub>	—	2.0	5.0	pF	
Gate resistance	R <sub>g</sub>	—	120	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1.0MHz
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Q <sub>g</sub>	—	223	—	pC	V <sub>DS</sub> = 10V, I <sub>D</sub> = 250mA
Gate-Source Charge	Q <sub>gs</sub>	—	82	—		
Gate-Drain Charge	Q <sub>gd</sub>	—	178	—		
<b>SWITCHING CHARACTERISTICS (Note 9)</b>						
Turn-On Delay Time	t <sub>D(on)</sub>	—	2.8	—	ns	V <sub>DD</sub> = 30V, I <sub>D</sub> = 0.2A, R <sub>L</sub> = 150Ω, V <sub>GEN</sub> = 10V, R <sub>GEN</sub> = 25Ω
Turn-On Rise Time	t <sub>r</sub>	—	3.0	—		
Turn-Off Delay Time	t <sub>D(off)</sub>	—	7.6	—		
Turn-Off Fall Time	t <sub>f</sub>	—	5.6	—		

- Notes: 6. Device mounted on FR-4 PCB, with minimum recommended pad layout  
7. Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.  
8. Short duration pulse test used to minimize self-heating effect.  
9. Guaranteed by design. Not subject to product testing.

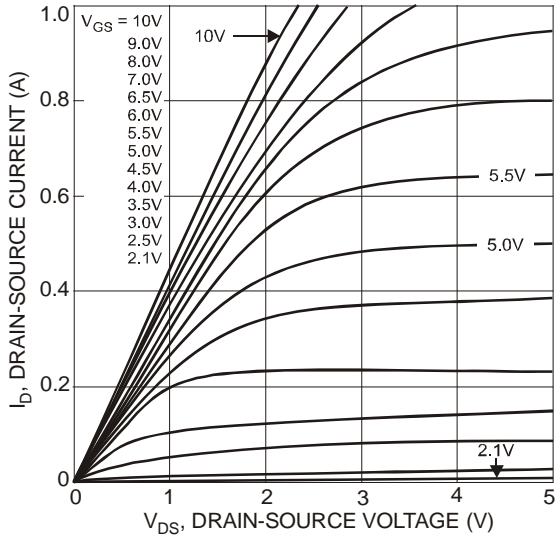


Fig. 1 On-Region Characteristics

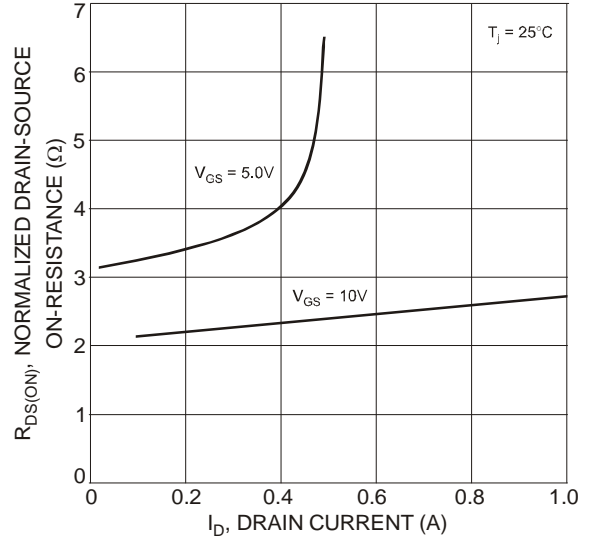


Fig. 2 On-Resistance vs. Drain Current

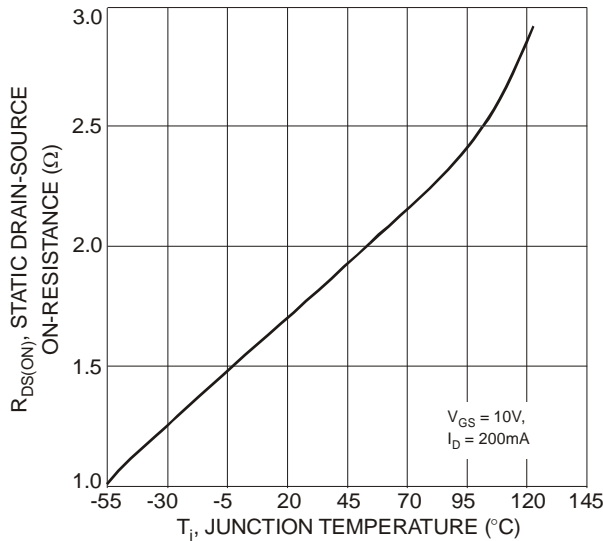


Fig. 3 On-Resistance vs. Junction Temperature

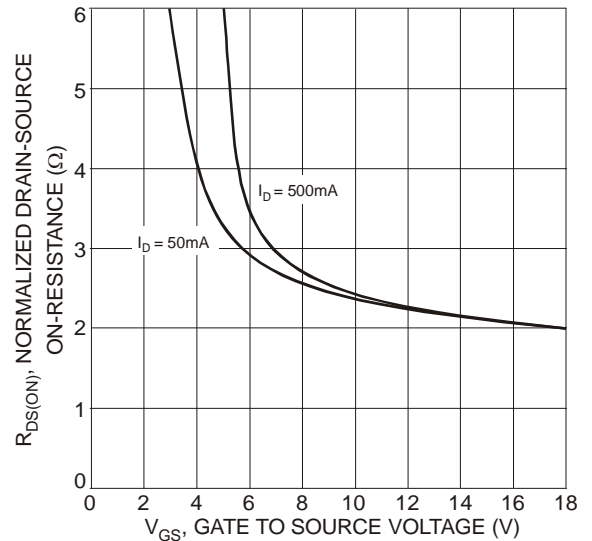


Fig. 4 On-Resistance vs. Gate-Source Voltage

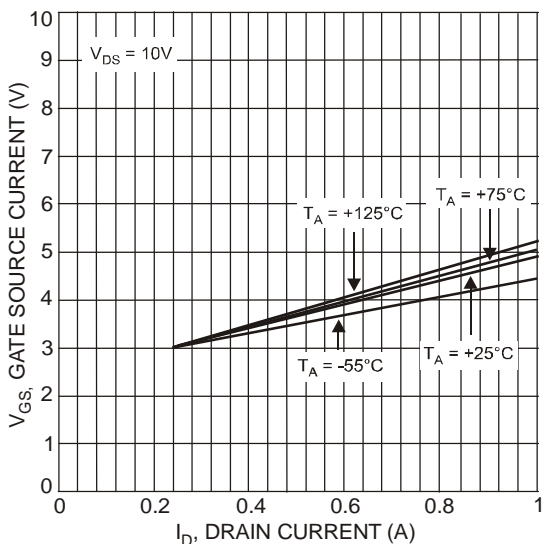


Fig. 5 Typical Transfer Characteristics

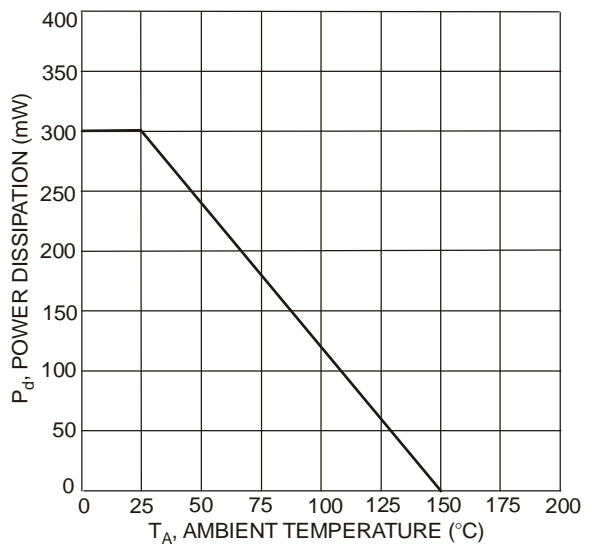
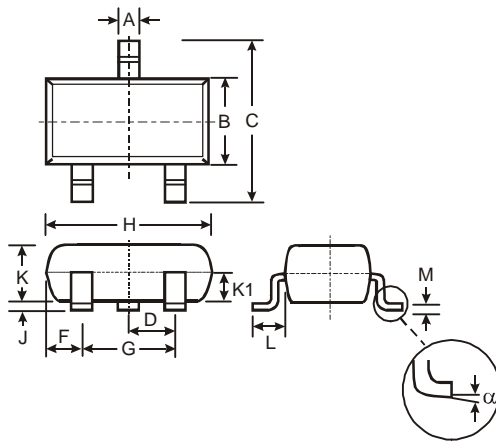


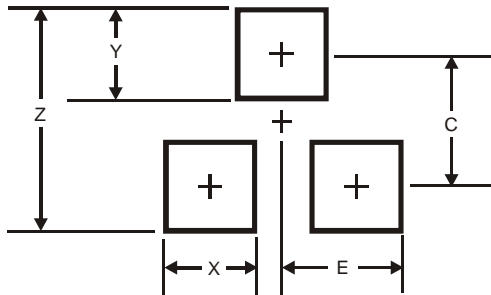
Fig. 6 Max Power Dissipation vs. Ambient Temperature

**Package Outline Dimensions**



SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.903	1.10	1.00
K1	-	-	0.400
L	0.45	0.61	0.55
M	0.085	0.18	0.11
α	0°	8°	-
All Dimensions in mm			

**Suggested Pad Layout**



Dimensions	Value (in mm)
Z	2.9
X	0.8
Y	0.9
C	2.0
E	1.35

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